

	L #	Hits	Search Text	DBs	Time Stamp
1	L51	27	((three two) adj step adj (oxidation)) and (semiconductor si silicon)) and (gate adj2 (insulat\$3 dielectric oxide dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 20:45
2	L58	13127	((reduc\$3 decreas\$3 slow\$3) near3 rate) near12 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 20:49
3	L65	1	51 and kielin.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 20:41
4	L72	79386	(gate adj2 (insulat\$3 dielectric oxide dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 20:45
5	L79	201	58 and 72	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 20:45
6	L86	14063	(reduc\$3 decreas\$3 slow\$3 lower lowered lowering chang\$3) near3 rate near8 heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:38
7	L93	121	72 and 86	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:16
8	L100	7	58 near12 (prevent\$3 near4 (overshoot\$3 overrun\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:21
9	L107	25141	(reduc\$3 decreas\$3 slow\$3 lower lowered lowering chang\$3) near3 rate near12 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:20
10	L114	10	107 near12 (prevent\$3 near4 (overshoot\$3 overrun\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:26
11	L121	194	(RTA RTP RTO (rapid adj thermal adj (anneal\$3 oxidation oxidiz\$3 oxidis\$3 process\$3))) near15 (control\$4 near3 (temperature rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:31
12	L128	36613	(reduc\$3 decreas\$3 slow\$3 lower lowered lowering chang\$3 modulat\$3 var\$4) near3 rate near8 (temperature or heat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:40
13	L135	3425	(time near2 temperature) near4 (profile plot\$4 graph\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:41
14	L142	18	121 and 128	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:41
15	L149	67	72 and 135	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:57